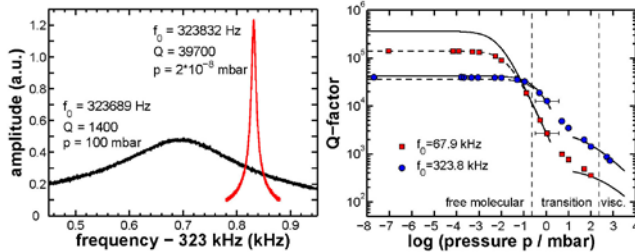


雰囲気中NC-AFMのQ値の気圧依存性

Pressure Dependence of the Q-factor of Cantilevers Used for NC-AFM (Conference -NC-AFM2010-)

Jannis Lübbe, Holger Schnieder and Michael Reichling, Vol. 9, pp. 30-33 (9 February, 2011)

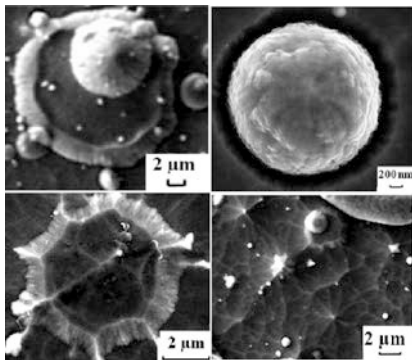


アーク放電蒸発によるTiN薄膜の成膜

Establishing the Relationship between Substrate Bias Voltage and Formation Process of Single Component Ion-Plasma's Film Based on Tin by Electric-Arc Evaporation (Regular Paper)

Vol. 9, pp. 34-39 (11 February, 2011)

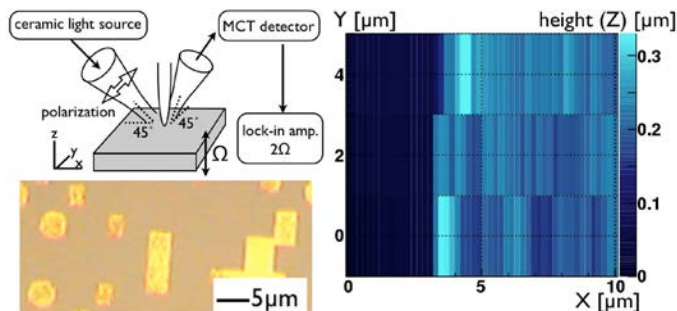
A. L. Kameneva, L. N. Guselnikova and T. O. Soshina,



フーリエ変換型赤外分光と近接場顕微鏡を結合

Application of a Modulating Technique to Detect Near-Field Signals Using a Conventional IR Spectrometer with a Ceramic Light Source (Conference -NSS-6-) Vol. 9, pp. 40-45 (11 February, 2011)

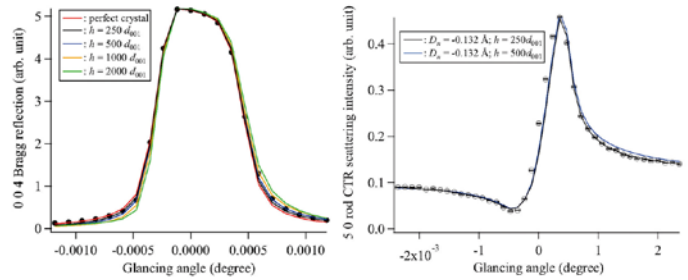
M. Ishikawa, M. Katsura, S. Nakashima, K. Aizawa, T. Inoue, Y. Ikemoto and H. Okamura



SiO₂/Si 界面での歪みを多波X線回折法で解析

Mesoscopic-Scale and Small Strain Field beneath SiO₂/Si Interface Revealed by a Multiple-Wave X-ray Diffraction Phenomenon — Depth of the Strain Field (Conference -Atomic Holography-2010-)

Vol. 9, pp. 47-50 (19 February, 2011) W. Yashiro, Y. Yoda, T. Takahashi, A. Teramoto, T. Hattori and K. Miki

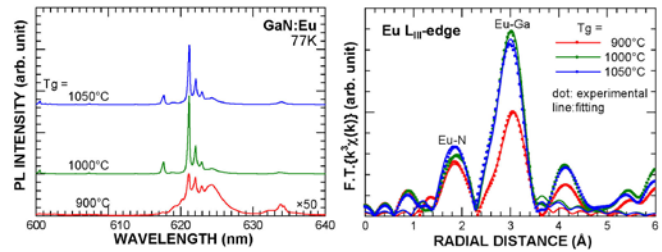


Eu ドープされた GaN の局所構造と PL 特性

Fluorescence XAFS Analysis of Eu-Doped GaN Layers Grown by Organometallic Vapor Phase Epitaxy

(Conference -NSS-6-) Vol. 9, pp. 51-53 (19 February, 2011)

H. Ofuchi, T. Honma, T. Kawasaki, N. Furukawa, A. Nishikawa and Y. Fujiwara

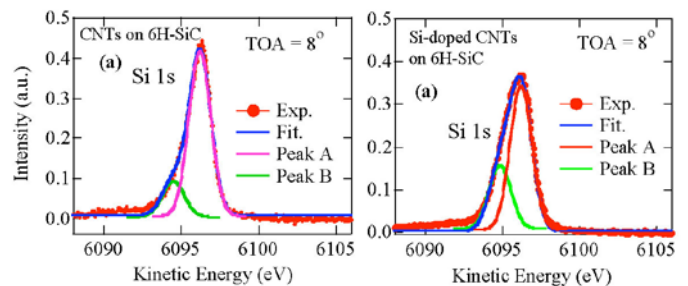


CNTにドープされたSiはsp²的結合

Chemical State Analysis of Si-Doped CNT on SiC by Hard X-Ray Photoelectron Spectroscopy

(Conference -NSS-6-) Vol. 9, pp. 54-57 (19 February, 2011)

J.-Y. Son, M. Machida, H. Oji, Y. Watanabe, T. Maruyama, W. Norimatsu and M. Kusunoki



解離エタノールによるグラフェンのガスソースMBE成長

Evaluation of Few-Layer Graphene Grown by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol (Conference -NSS-6-)

Vol. 9, pp. 58-62 (26 February, 2011)

F. Maeda, H. Hibino, I. Hirose and Y. Watanabe

